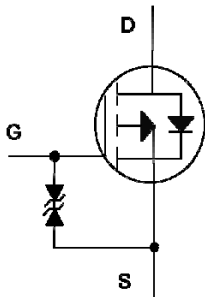
杰力科技股份有限公司
Excelliance MOS Corporation

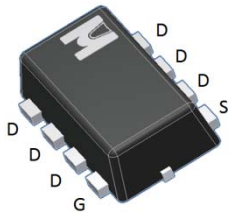
**EMZB20P03L**

**P-Channel Logic Level Enhancement Mode Field Effect Transistor**

Product Summary:

| | |
|---|---|
| $BV_{DSS}$ | -30V |
| $R_{DSON\ (MAX.)}$ | 24mΩ |
| $I_D$ | -8A |




UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ESD Protection

**ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C Unless Otherwise Noted)**

| PARAMETERS/TEST CONDITIONS | | SYMBOL | LIMITS | UNIT |
|---|---|---|---|---|
| Gate-Source Voltage | | $V_{GS}$ | ±25 | V |
| Continuous Drain Current | $T_A$ = 25 °C | $I_D$ | -8 | A |
| | $T_A$ = 70 °C | | -6 | |
| Pulsed Drain Current[1] | | $I_{DM}$ | -32 | |
| Avalanche Current | | $I_{AS}$ | -10 | |
| Avalanche Energy | L = 0.1mH, $I_D$=-10A, $R_G$=25Ω | $E_{AS}$ | 5 | mJ |
| Repetitive Avalanche Energy[2] | L = 0.05mH | $E_{AR}$ | 2.5 | |
| Power Dissipation[3] | $T_A$ = 25 °C | $P_D$ | 2.5 | W |
| | $T_A$ = 70 °C | | 1 | |
| Operating Junction & Storage Temperature Range | | $T_j$, $T_{stg}$ | -55 to 150 | °C |

**THERMAL RESISTANCE RATINGS**

| THERMAL RESISTANCE | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
|---|---|---|---|---|---|
| Junction-to-Lead | Steady-State | $R_{\theta JL}$ | | 30 | °C / W |
| Junction-to-Ambient[4] | t ≦ 10s | $R_{\theta JA}$ | | 50 | |
| | Steady-State | | | 90 | |

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

[3]The power dissipation PD is based on $T_{J(MAX)}$=150°C, using ≦10s junction-to-ambient thermal resistance.

[4]The value of $R_{\theta JA}$ is measured with mounted on a 1 $in^2$ pad of 2 oz copper.

**ELECTRICAL CHARACTERISTICS ($T_J$ = 25 °C, Unless Otherwise Noted)**

| PARAMETER | SYMBOL | TEST CONDITIONS | LIMITS | | | UNIT |
|---|---|---|---|---|---|---|
| | | | MIN | TYP | MAX | |
| **STATIC** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ = -250μA | -30 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = -250μA | -1 | -1.5 | -3 | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0V, $V_{GS}$ = ±20V | | | ±30 | μA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = -24V, $V_{GS}$ = 0V | | | -1 | μA |
| | | $V_{DS}$ = -20V, $V_{GS}$ = 0V, $T_J$ = 125 °C | | | -10 | |
| On-State Drain Current[1] | $I_{D(ON)}$ | $V_{DS}$ = -5V, $V_{GS}$ = -10V | -8 | | | A |
| Drain-Source On-State Resistance[1] | $R_{DS(ON)}$ | $V_{GS}$ = -10V, $I_D$ = -8A | | 20 | 24 | mΩ |
| | | $V_{GS}$ = -4.5V, $I_D$ = -7A | | 29 | 38 | |
| Forward Transconductance[1] | $g_{fs}$ | $V_{DS}$ = -5V, $I_D$ = -8A | | 24 | | S |
| **DYNAMIC** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0V, $V_{DS}$ = -15V, f = 1MHz | | 1407 | | pF |
| Output Capacitance | $C_{oss}$ | | | 208 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 164 | | |
| Gate Resistance | $R_g$ | $V_{GS}$ = 15mV, $V_{DS}$ = 0V, f = 1MHz | | 4.5 | | Ω |
| Total Gate Charge[1,2] | $Q_g$($V_{GS}$=10V) | $V_{DS}$ = -15V, $V_{GS}$ = -10V, $I_D$ = -8A | | 20.3 | | nC |
| | $Q_g$($V_{GS}$=4.5V) | | | 10 | | |
| Gate-Source Charge[1,2] | $Q_{gs}$ | | | 3.2 | | |
| Gate-Drain Charge[1,2] | $Q_{gd}$ | | | 4.9 | | |
| Turn-On Delay Time[1,2] | $t_{d(on)}$ | $V_{DS}$ = -15V, $I_D$ = -1A, $V_{GS}$ = -10V, $R_{GS}$ = 2.7Ω | | 10 | | nS |
| Rise Time[1,2] | $t_r$ | | | 8 | | |
| Turn-Off Delay Time[1,2] | $t_{d(off)}$ | | | 25 | | |
| Fall Time[1,2] | $t_f$ | | | 6 | | |
| **SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C$ = 25 °C)** | | | | | | |
| Continuous Current | $I_S$ | | | | -3 | A |
| Pulsed Current[3] | $I_{SM}$ | | | | -12 | |
| Forward Voltage[1] | $V_{SD}$ | $I_F$ = $I_S$ A, $V_{GS}$ = 0V | | | -1.2 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_F$ = $I_S$, $dI_F/dt$ = 100A / μS | | 32 | | nS |
| Reverse Recovery Charge | $Q_{rr}$ | | | 26 | | nC |

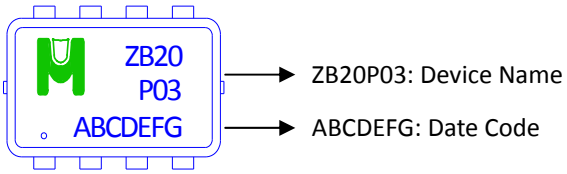
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

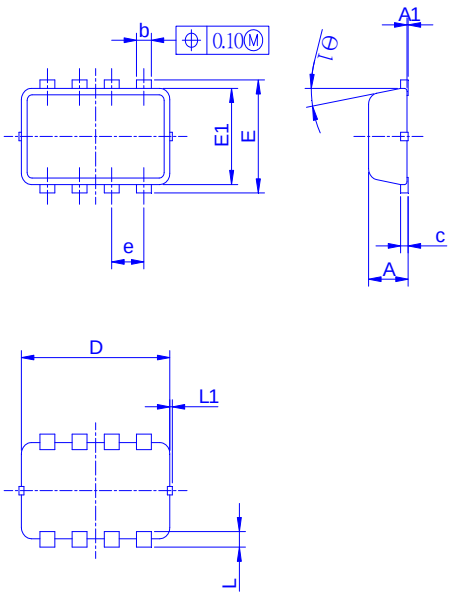
[3]Pulse width limited by maximum junction temperature.

## Ordering & Marking Information:

Device Name: EMZB20P03L for DFN 3 x 2



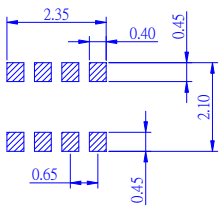

## Outline Drawing



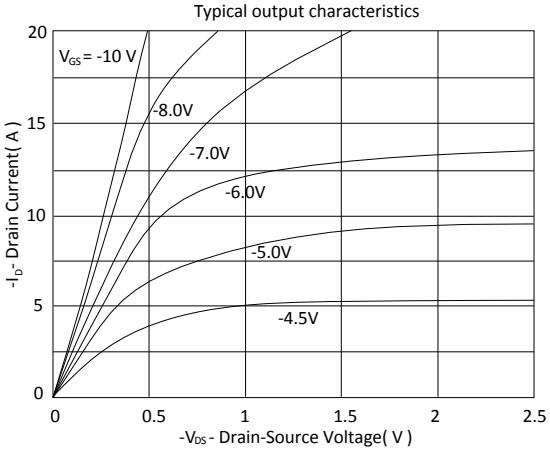

Dimension in mm

| Dimension | A | A1 | b | c | D | E | E1 | e | L | L1 | θ1 |
|---|---|---|---|---|---|---|---|---|---|---|---|
| Min. | 0.70 | 0.00 | 0.24 | 0.08 | | | | | 0.20 | 0.00 | 0° |
| Typ. | | | | | 3.00 | 2.00 | 1.70 | 0.65 | | | |
| Max. | 0.90 | 0.05 | 0.35 | 0.25 | | | | | 0.40 | 0.10 | 12° |

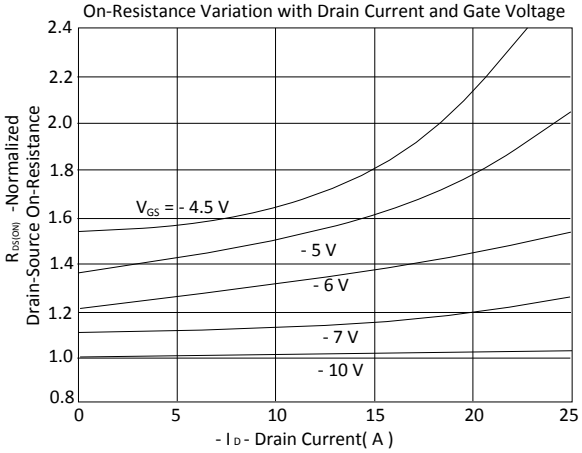
## Recommended minimum pads



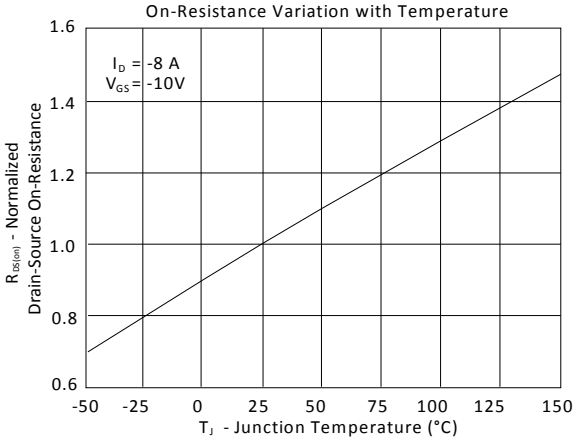
Typical output characteristics



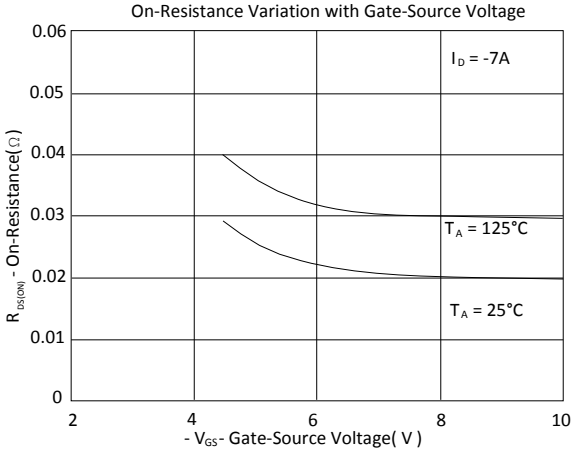

On-Resistance Variation with Drain Current and Gate Voltage



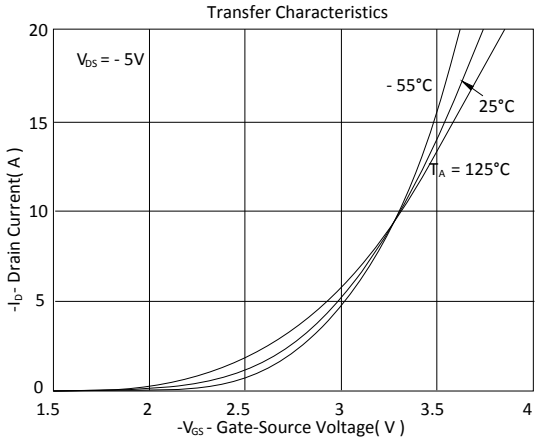

On-Resistance Variation with Temperature



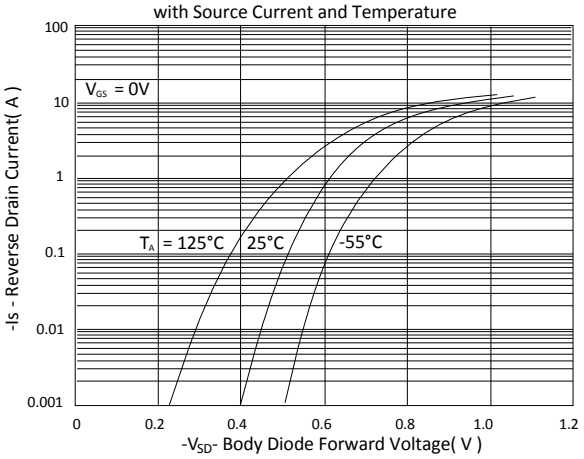

On-Resistance Variation with Gate-Source Voltage



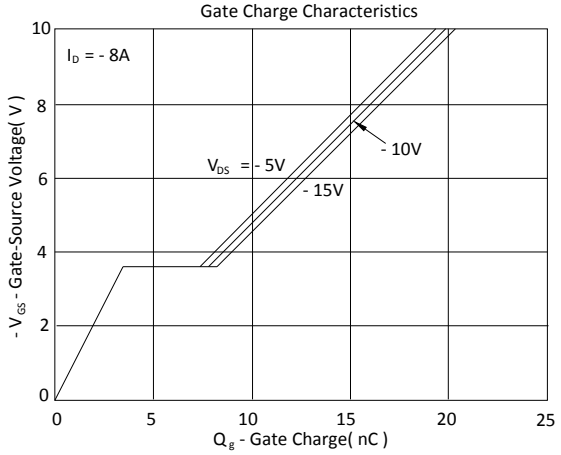

Transfer Characteristics



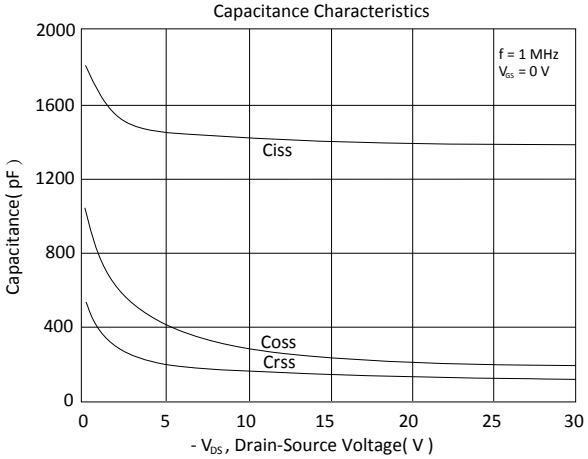

Body Diode Forward Voltage Variation with Source Current and Temperature



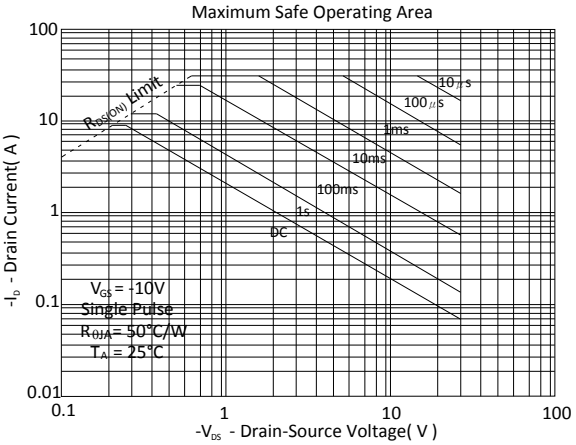
Gate Charge Characteristics



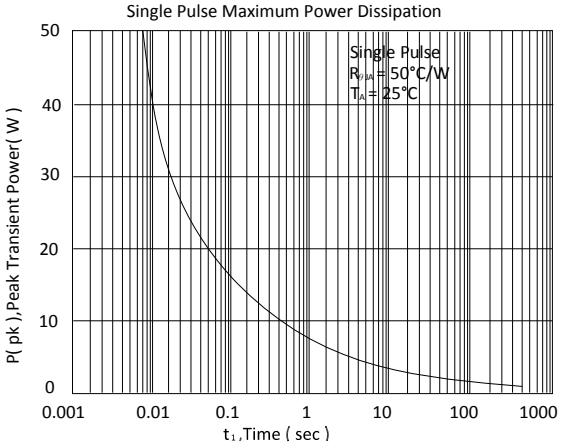

Capacitance Characteristics




Maximum Safe Operating Area




Single Pulse Maximum Power Dissipation




Transient Thermal Response Curve